N-Channel Silicon MOSFET



**CPH6405** 

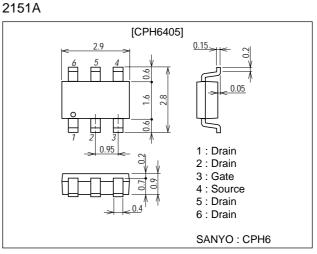
# **Ultrahigh-Speed Switching Applications**

## Features

- Low ON-state resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

## **Package Dimensions**

unit : mm



## Specifications Absolute Maximum Ratings at Ta=25°C

| Parameter                   | Symbol         | Conditions   | Ratings     | Unit |
|-----------------------------|----------------|--|-------------|------|
| Drain-to-Source Voltage     | VDSS           |  | 30          | V    |
| Gate-to-Source Voltage      | VGSS           |  | ±10         | V    |
| Drain Current (DC)          | ۱ <sub>D</sub> |  | 6           | А    |
| Drain Current (Pulse)       | IDP            | PW≤10µs, duty cycle≤1%                                 | 24          | А    |
| Allowable Power Dissipation | PD             | Mounted on a ceramic board (900mm <sup>2</sup> X0.8mm) | 1.6         | W    |
| Channel Temperature         | Tch            |  | 150         | °C   |
| Storage Temperature         | Tstg           |  | -55 to +150 | °C   |

### Electrical Characteristics at Ta=25°C

| Parameter                                  | Symbol                | Conditions                                | Ratings |     |     | Unit |
|--|-----------------------|---|---------|-----|-----|------|
|  |                       |   | min     | typ | max | Unit |
| Drain-to-Source Breakdown Voltage          | V(BR)DSS              | ID=1mA, VGS=0                             | 30      |     |     | V    |
| Zero-Gate Voltage Drain Current            | IDSS                  | V <sub>DS</sub> =30V, V <sub>GS</sub> =0  |         |     | 1   | μΑ   |
| Gate-to-Source Leakage Current             | IGSS                  | VGS=±8V, VDS=0                            |         |     | ±10 | μΑ   |
| Cutoff Voltage                             | VGS(off)              | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA | 0.4     |     | 1.3 | V    |
| Forward Transfer Admittance                | yfs                   | V <sub>DS</sub> =10V, I <sub>D</sub> =3A  | 6.3     | 9   |     | S    |
| Static Drain-to-Source On-State Resistance | RDS(on)1              | ID=3A, VGS=4V                             |         | 33  | 43  | mΩ   |
|  | R <sub>DS</sub> (on)2 | I <sub>D</sub> =1A, V <sub>GS</sub> =2.5V |         | 43  | 61  | mΩ   |

Marking : KE

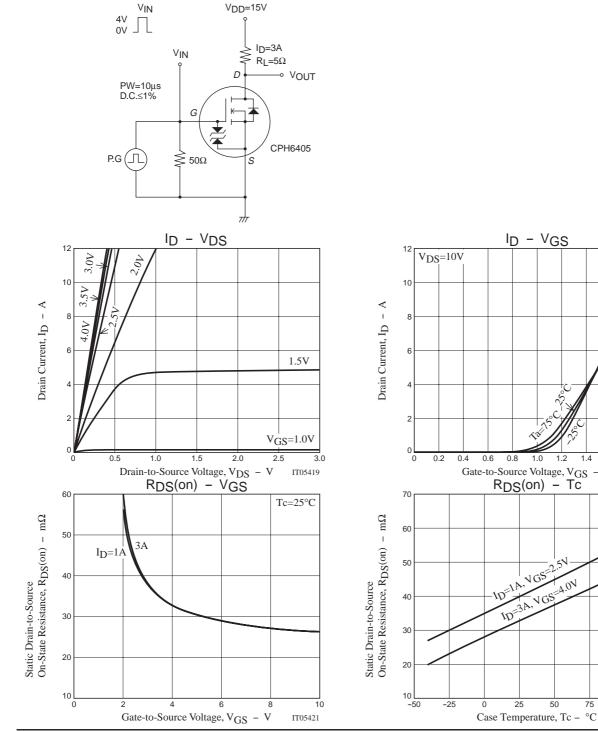
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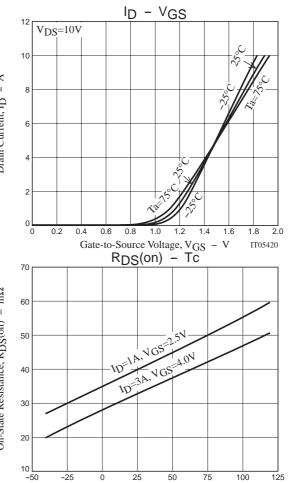
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| Parameter                     | Symbol              | Conditions   |     | Ratings |     |      |
|-------------------------------|---------------------|--|-----|---------|-----|------|
|                               | Symbol              |  | min | typ     | max | Unit |
| Input Capacitance             | Ciss                | V <sub>DS</sub> =10V, f=1MHz                                   |     | 560     |     | pF   |
| Output Capacitance            | Coss                | V <sub>DS</sub> =10V, f=1MHz                                   |     | 120     |     | pF   |
| Reverse Transfer Capacitance  | Crss                | V <sub>DS</sub> =10V, f=1MHz                                   |     | 70      |     | pF   |
| Turn-ON Delay Time            | t <sub>d</sub> (on) | See specified Test Circuit.                                    |     | 12      |     | ns   |
| Rise Time                     | tr                  | See specified Test Circuit.                                    |     | 135     |     | ns   |
| Turn-OFF Delay Time           | td(off)             | See specified Test Circuit.                                    |     | 50      |     | ns   |
| Fall Time                     | tf                  | See specified Test Circuit.                                    |     | 110     |     | ns   |
| Total Gate Charge             | Qg                  | V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A |     | 24      |     | nC   |
| Gate-to-Source Charge         | Qgs                 | V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A |     | 1.5     |     | nC   |
| Gate-to-Drain "Miller" Charge | Qgd                 | V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A |     | 3.2     |     | nC   |
| Diode Forward Voltage         | V <sub>SD</sub>     | IS=6A, VGS=0   |     |         | 1.2 | V    |

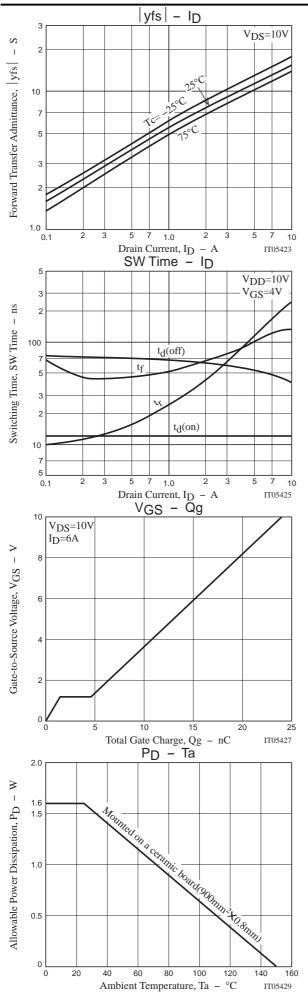
#### **Switching Time Test Circuit**

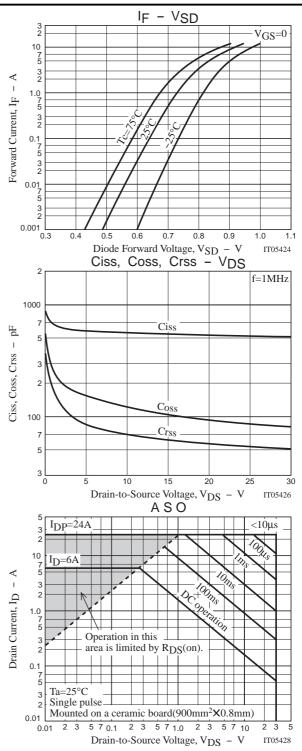




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